TOSHIBA

TOSHIBA Transistor Silicon PNP Epitaxial Type (PCT process)

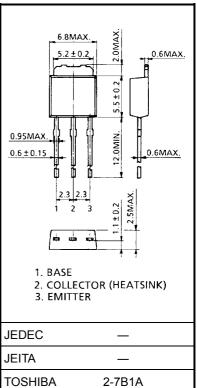
# 2SB905

**Power Amplifier Applications** 

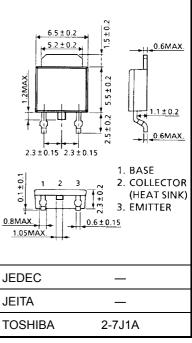
• Complementary to SD1220

#### Maximum Ratings (Ta = 25°C)

Characteristics		Symbol	Rating	Unit	
Collector-base voltage		V <sub>CBO</sub>	-150	V	
Collector-emitter voltage		V <sub>CEO</sub>	-150	V	
Emitter-base voltage		V <sub>EBO</sub>	-6	V	
Collector current		Ι <sub>C</sub>	-1.5	А	
Base current		Ι <sub>Β</sub>	-1.0	А	
Collector power dissipation	Ta = 25°C	Pc	1.0	W	
	Tc = 25°C	ГС	10		
Junction temperature		Tj	150	°C	
Storage temperature range		T <sub>stg</sub>	-55 to 150	°C	



Weight: 0.36 g (typ.)



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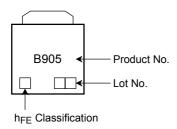
Unit: mm

## **Electrical Characteristics (Ta = 25°C)**

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Collector cut-off current	I <sub>CBO</sub>	V <sub>CB</sub> = −150 V, I <sub>E</sub> = 0	_	_	-1.0	μA
Emitter cut-off current	I <sub>EBO</sub>	$V_{EB} = -6 V, I_C = 0$	_	_	-1.0	μA
Collector-emitter breakdown voltage	V (BR) CEO	I <sub>C</sub> = -10 mA, I <sub>B</sub> = 0	-150	-	—	V
DC current gain	h <sub>FE</sub> (Note)	V <sub>CE</sub> = -5 V, I <sub>C</sub> = -200 mA	60		320	
Collector-emitter saturation voltage	V <sub>CE (sat)</sub>	I <sub>C</sub> = -500 mA, I <sub>B</sub> = -50 mA	_	_	-1.5	V
Base-emitter voltage	V <sub>BE</sub>	$V_{CE} = -5 V, I_C = -5 mA$	-0.5	_	-0.8	V
Transition frequency	f <sub>T</sub>	$V_{CE}$ = -5 V, I <sub>C</sub> = -200 mA	15	50	_	MHz
Collector output capacitance	C <sub>ob</sub>	$V_{CB}$ = -10 V, I <sub>E</sub> = 0, f = 1 MHz	-	_	35	pF

Note: hFE classification R: 60 to 120, O: 100 to 200, Y: 160 to 320

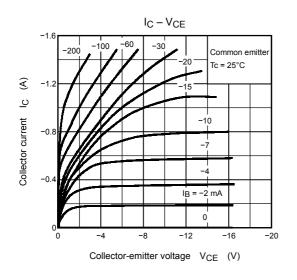
### Marking

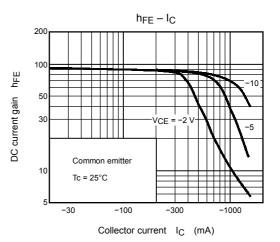


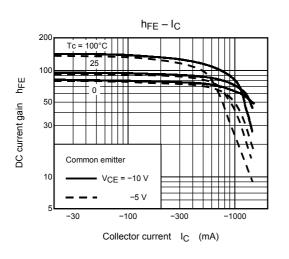
### Explanation of Lot No.

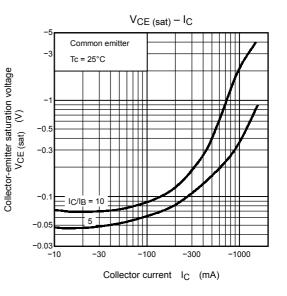
Month of manufacture: January to December are denoted by letters A to L respectively. Year of manufacture: last decimal digit of the year of manufacture

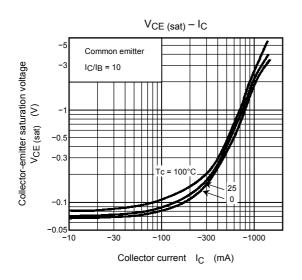
# **TOSHIBA**

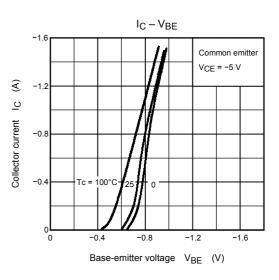




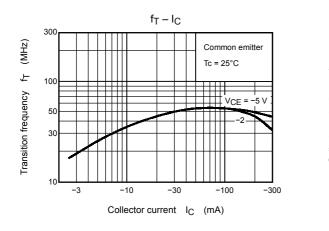


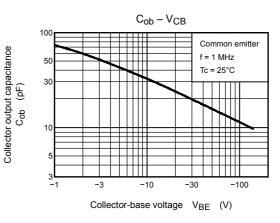


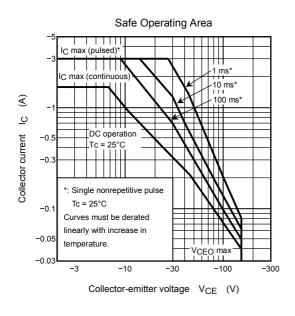




# **TOSHIBA**







P<sub>C</sub> – Ta 12 (1) Tc = Ta infinite heat sink (2) Ceramic substrate Ś (1) 50 × 50 × 0.8 mm 10 (3) No heat sink РС Collector power dissipation (2) (3) 0 0 25 175 50 75 150 100 125 Ambient temperature Ta (°C)

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